Pj Zampardi

List of Publications by Year in descending order

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		1163117	1058476	
18	219	8	14	
papers	citations	h-index	g-index	
18	18	18	110	
all docs	docs citations	times ranked	citing authors	

#	Article	IF	CITATIONS
1	A comparison of linear handset power amplifiers in different bipolar technologies. IEEE Journal of Solid-State Circuits, 2004, 39, 1746-1754.	5.4	54
2	A Broad-Band Lumped Element Analytic Model Incorporating Skin Effect and Substrate Loss for Inductors and Inductor Like Components for Silicon Technology Performance Assessment and RFIC Design. IEEE Transactions on Electron Devices, 2005, 52, 1429-1441.	3.0	33
3	40 Gbit/s AlGaAs/GaAs HBT 4:1 multiplexer IC. Electronics Letters, 1995, 31, 876-877.	1.0	28
4	An InGaP/GaAs Merged HBT-FET (BiFET) Technology and Applications to the Design of Handset Power Amplifiers. IEEE Journal of Solid-State Circuits, 2007, 42, 2137-2148.	5.4	19
5	Delay of Kirk effect due to collector current spreading in heterojunction bipolar transistors. IEEE Electron Device Letters, 1996, 17, 470-472.	3.9	18
6	Role of neutral base recombination in high gain AlGaAs/GaAs HBT's. IEEE Transactions on Electron Devices, 1999, 46, 1599-1607.	3.0	14
7	High performance Al/sub 0.35/Ga/sub 0.65/As/GaAs HBT's. IEEE Electron Device Letters, 2000, 21, 196-199.	3.9	11
8	A GaAs Junction Varactor With a Continuously Tunable Range of 9 : 1 and an \$OIP_{3}\$ of 57 dBm. IEEE Electron Device Letters, 2010, 31, 108-110.	3.9	11
9	Packaged 30 Gbit/s data demultiplexing and clock extraction IC fabricated in a AlGaAs/GaAs HBT technology. Electronics Letters, 1996, 32, 588.	1.0	6
10	A packaged broad-band monolithic variable gain amplifier implemented in AlGaAs/GaAs HBT technology. IEEE Journal of Solid-State Circuits, 1996, 31, 1380-1387.	5.4	5
11	30 Gbit/s 1:4 demultiplexer IC using AlGaAs/GaAs HBTs. Electronics Letters, 1997, 33, 765.	1.0	5
12	Heterostructure-based high-speed/high-frequency electronic circuit applications. Solid-State Electronics, 1999, 43, 1633-1643.	1.4	4
13	High efficiency current-mode class-D amplifier with integrated resonator. , 0, , .		4
14	Ultra Highspeed AlGaAs/GaAs HBT Circuits For Up To 40 Gb/s Optical Communications. , 1997, , .		3
15	Monolithically integrated HBT/MESFET circuit. Electronics Letters, 1993, 29, 1100.	1.0	2
16	Circuit demonstrations in a GaAs BiFET technology. Solid-State Electronics, 1995, 38, 1723-1726.	1.4	1
17	16 GHz low-power 1:4 prescalar fabricated in 1.0 [micro sign]m BiFET technology. Electronics Letters, 2001, 37, 389.	1.0	1
18	Technology design interaction. , 2016, , 209-259.		0